NTHD4102P

[MOSFET](#) – Dual, P-Channel, ChipFET

-20 V, -4.1 A

ON Semiconductor®

V(BR)DSS	RDS(ON) TYP	ID MAX
−20 V	64 mΩ @ −4.5 V	−4.1 A
	85 mΩ @ −2.5 V	
	120 mΩ @ −1.8 V	

Features

- Offers an Ultra Low $R_{DS(ON)}$ Solution in the ChipFET Package
- Miniature ChipFET Package 40% Smaller Footprint than TSOP−6
- Low Profile (<1.1 mm) Allows it to Fit Easily into Extremely Thin Environments such as Portable Electronics
- Simplifies Circuit Design since Additional Boost Circuits for Gate Voltages are not Required
- Operated at Standard Logic Level Gate Drive, Facilitating Future Migration to Lower Levels using the same Basic Topology
- Pb−Free Package is Available

Applications

- Optimized for Battery and Load Management Applications in Portable Equipment such as MP3 Players, Cell Phones, and PDAs
- Charge Control in Battery Chargers
- Buck and Boost Converters

P−Channel MOSFET   P−Channel MOSFET

ChipFET CASE 1206A STYLE 2

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−20	V
Gate−to−Source Voltage			V_{GS}	±8.0	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−2.9	A
		T_A = 85°C		−2.1	
	t ≤ 10 s	T_A = 25°C		−4.1	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	1.1	W
	t ≤ 10 s			2.1	
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−16	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−1.1	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient, Steady State (Note 1)	$R_{\theta JA}$	113	°C/W
Junction−to−Ambient, t ≤ 10s (Note 1)		60	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
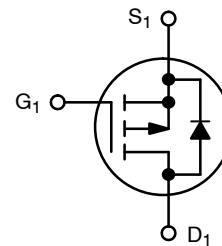1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
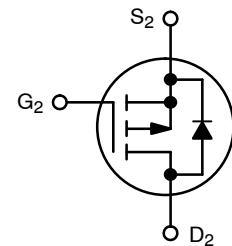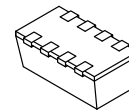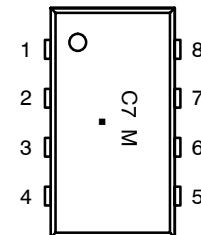
PIN CONNECTIONS

MARKING DIAGRAM

C7 = Specific Device Code
M = Month Code
■ = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTHD4102PT1	ChipFET	3000/Tape & Reel
NTHD4102PT1G	ChipFET (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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NTHD4102P

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(Br)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−20			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(Br)DSS}/T_J$				−15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V V_{DS} = −16 V	T_J = 25°C			−1.0	μA
			T_J = 85°C			−5.0	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8.0 V				±100	nA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.45		−1.5	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				2.7		mV/°C
Drain−to−Source On Resistance	$R_{DS(ON)}$	V_{GS} = −4.5 V, I_D = −2.9 A			64	80	mΩ
		V_{GS} = −2.5 V, I_D = −2.2 A			85	110	
		V_{DS} = −1.8 V, I_D = −1.0 A			120	170	
Forward Transconductance	g_{FS}	V_{DS} = −10 V, I_D = −2.9 A			7.0		S
CHARGES, CAPACITANCES, AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −16 V			750		pF
Output Capacitance	C_{OSS}				100		
Reverse Transfer Capacitance	C_{RSS}				45		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −16 V, I_D = −2.6 A			7.6	8.6	nC
Gate−to−Source Charge	Q_{GS}				1.3		
Gate−to−Drain Charge	Q_{GD}				2.6		
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −16 V, I_D = −2.6 A, R_G = 2.0 Ω			5.5	10	ns
Rise Time	t_r				12	25	
Turn−Off Delay Time	$t_{d(OFF)}$				32	40	
Fall Time	t_f				23	35	
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.1 A			−0.8	−1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 1.0 A			20	40	ns
Charge Time	ta				15		
Discharge Time	tb				5		
Reverse Recovery Charge	Q_{RR}				0.01		μC

2. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2%
3. Switching characteristics are independent of operating junction temperatures

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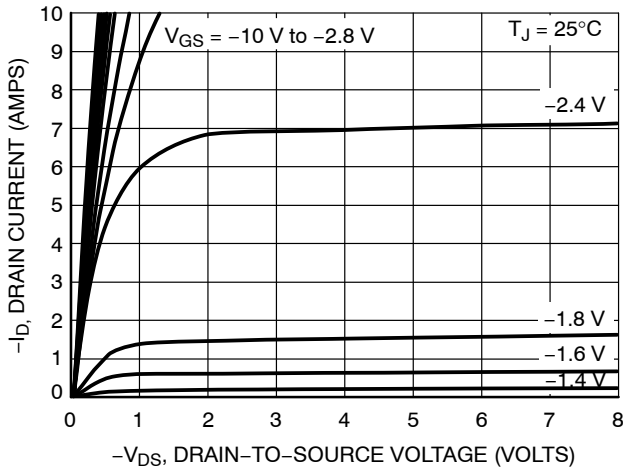## TYPICAL PERFORMANCE CURVES ($T_J = 25°C$ unless otherwise noted)
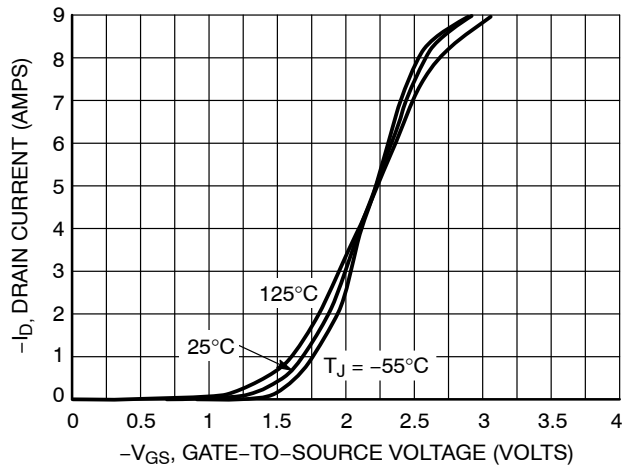
Figure 1. On−Region Characteristics
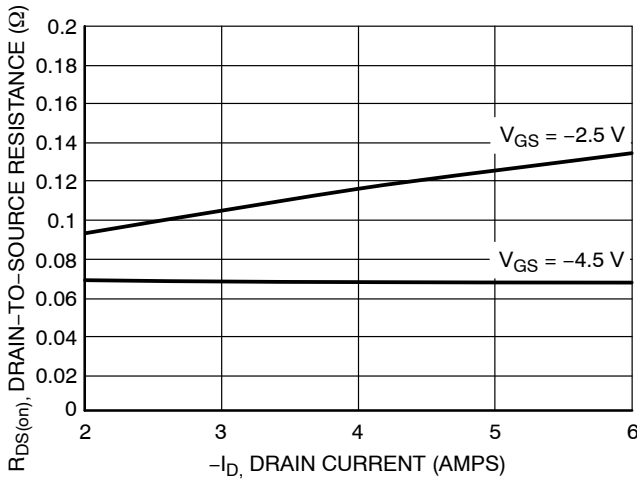
Figure 2. Transfer Characteristics

Figure 3. On−Resistance vs. Drain Current and Gate Voltage

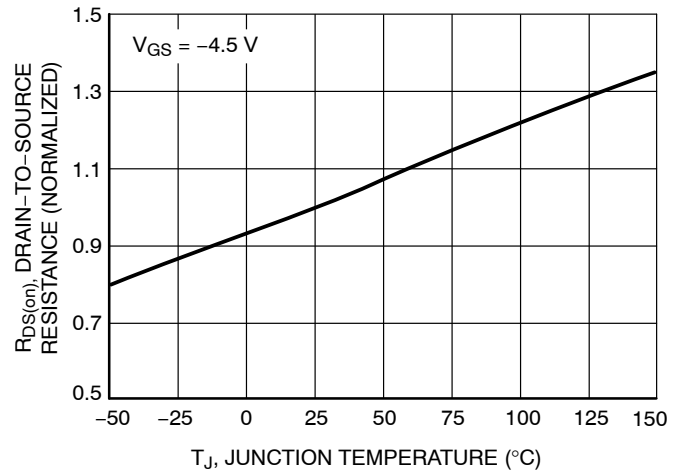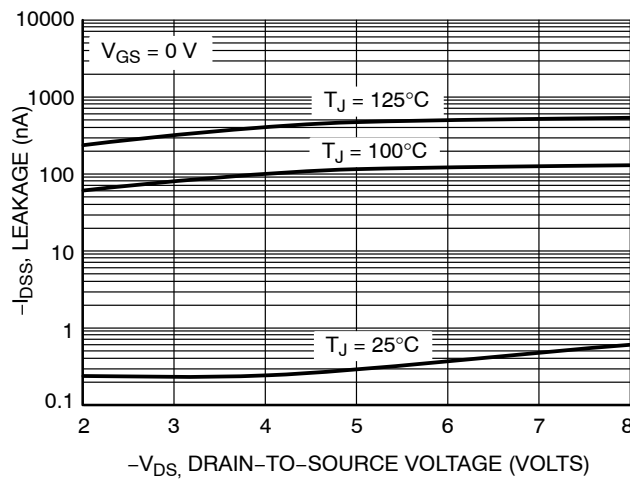**Figure 4. On−Resistance Variation with Temperature**

Figure 5. Drain−to−Source Leakage Current vs. Voltage

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TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)
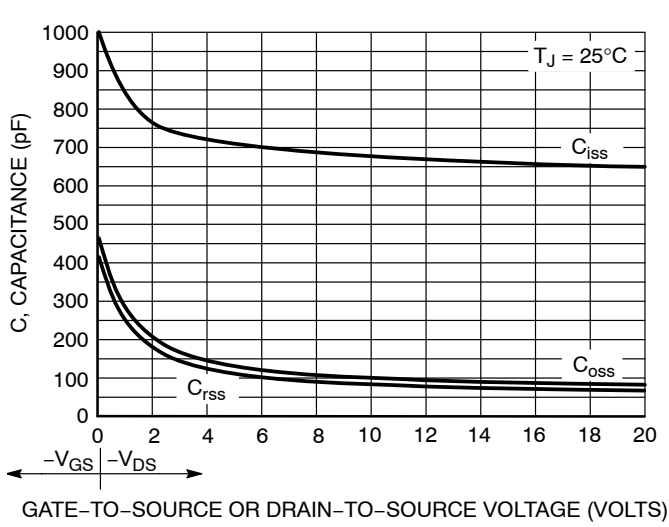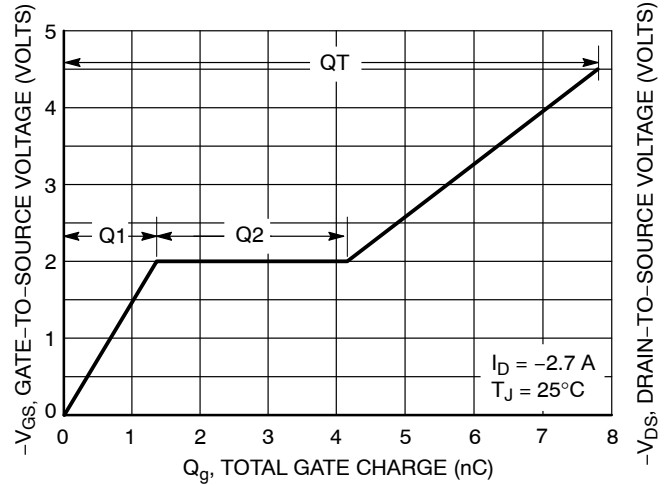

Figure 6. Capacitance Variation

Figure 7. Gate−to−Source and Drain−to−Source
Voltage vs. Total Gate Charge
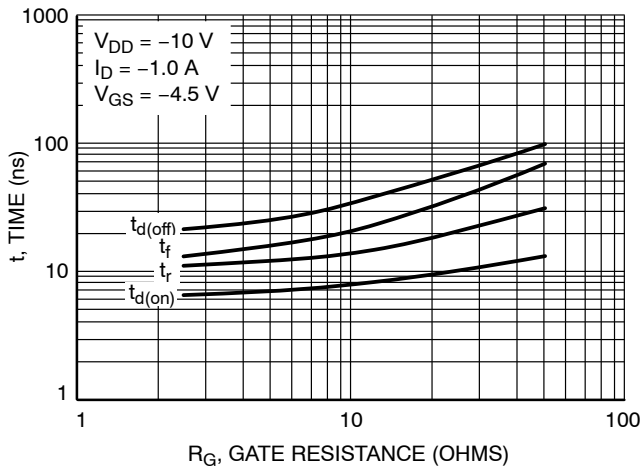
Figure 8. Resistive Switching Time Variation
vs. Gate Resistance
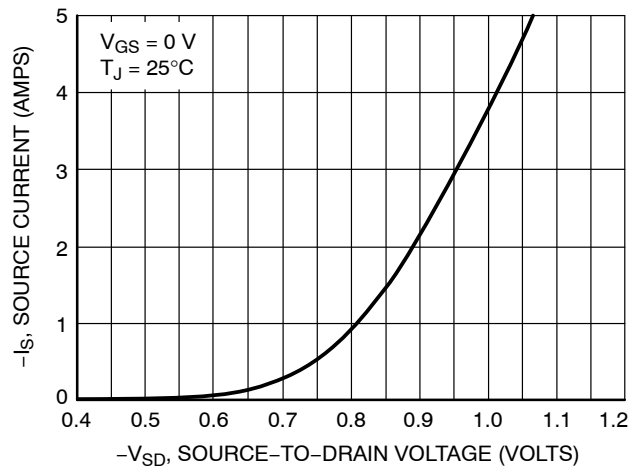
Figure 9. Diode Forward Voltage vs. Current
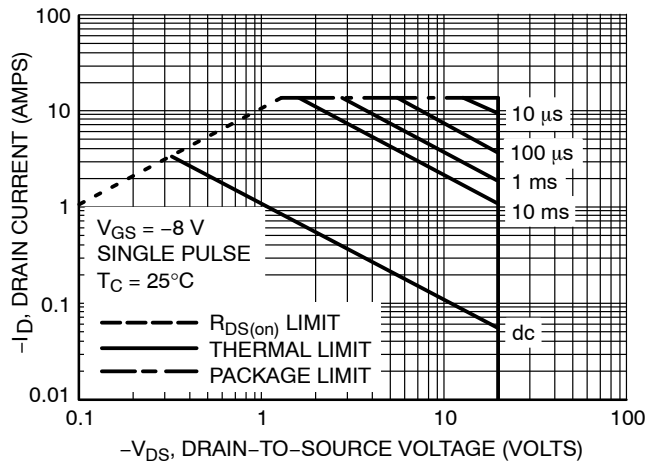
Figure 10. Maximum Rated Forward Biased
Safe Operating Area

ChipFET is a trademark of Vishay Siliconix.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

ChipFET™
CASE1206A–03
ISSUE K

DATE 19 MAY 2009

SCALE 1:1

RESET

$$\boxed{\triangle \quad 0.05\ (0.002)}$$
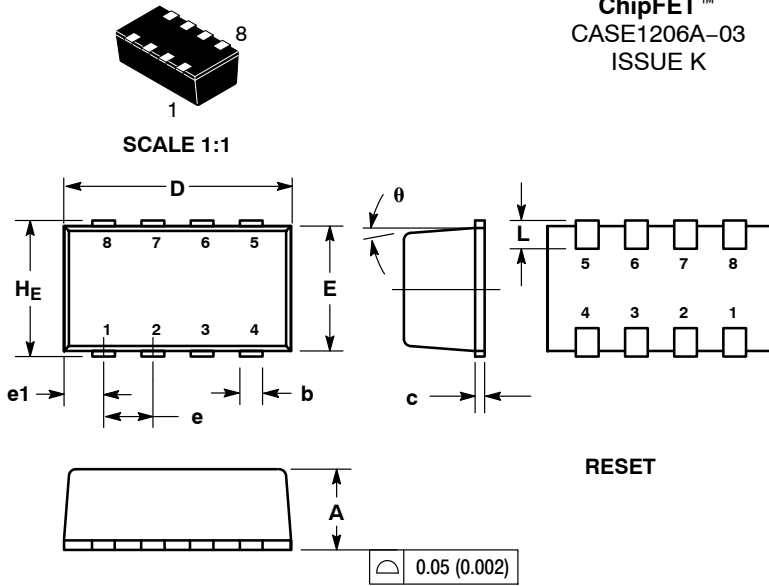
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.05	1.10	0.039	0.041	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.025 BSC		
e1	0.55 BSC			0.022 BSC		
L	0.28	0.35	0.42	0.011	0.014	0.017
H_E	1.80	1.90	2.00	0.071	0.075	0.079
θ	5° NOM			5° NOM		

STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. GATE
5. SOURCE
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 2:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 3:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. COLLECTOR
4. BASE
5. EMITTER
6. COLLECTOR
7. COLLECTOR
8. COLLECTOR

STYLE 5:
PIN 1. ANODE
2. ANODE
3. DRAIN
4. DRAIN
5. SOURCE
6. GATE
7. CATHODE
8. CATHODE

STYLE 6:
PIN 1. ANODE
2. DRAIN
3. DRAIN
4. GATE
5. SOURCE
6. DRAIN
7. DRAIN
8. CATHODE / DRAIN

SOLDERING FOOTPRINT

2.032 / 0.08

2.362 / 0.093

8X 0.457 / 0.018

8X 0.66 / 0.026

0.65 / 0.025 PITCH

$\left(\dfrac{mm}{inches}\right)$

Basic Style

GENERIC MARKING DIAGRAM*

xxx M▪
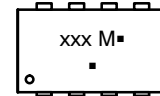
xxx = Specific Device Code
M = Month Code
▪ = Pb–Free Package
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ▪", may or may not be present.

OPTIONAL SOLDERING FOOTPRINTS ON PAGE 2

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DESCRIPTION:	ChipFET		PAGE 1 OF 2

ChipFET™
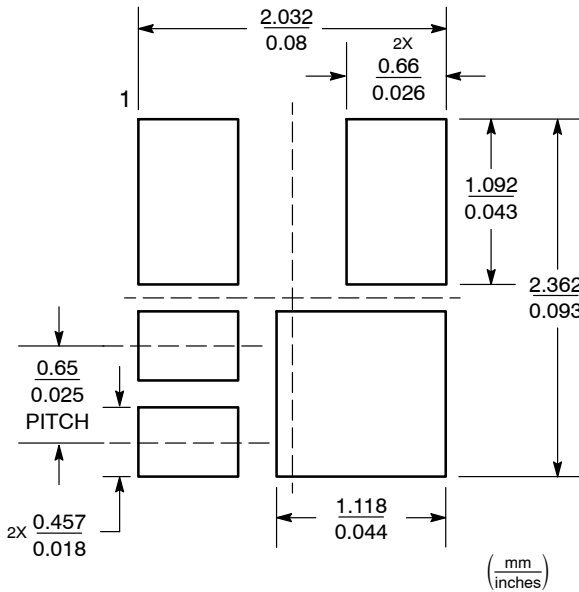CASE 1206A–03
ISSUE K

DATE 19 MAY 2009

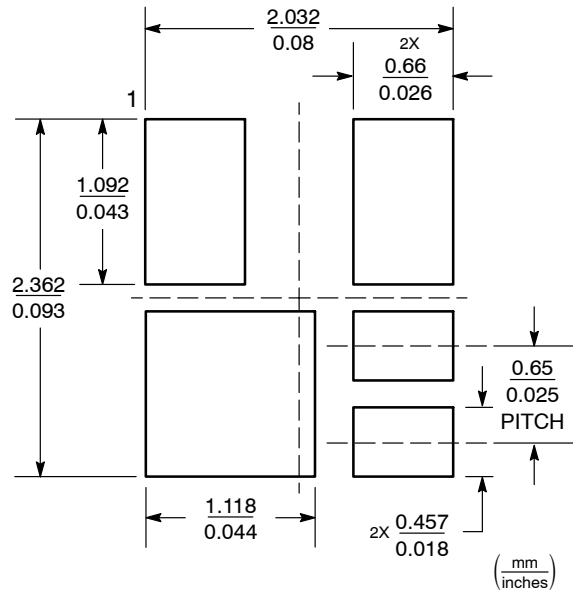## ADDITIONAL SOLDERING FOOTPRINTS*

Styles 1 and 4
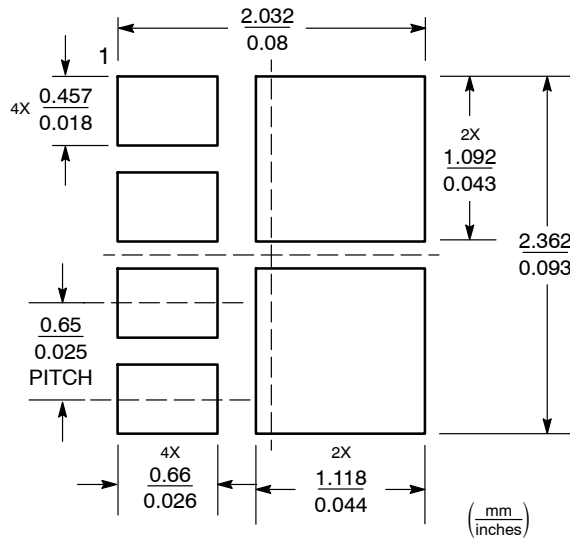
Style 2

Style 3

Style 5

*For additional information on our Pb–Free strategy and soldering
details, please download the ON Semiconductor Soldering and
Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	ChipFET		PAGE 2 OF 2

ADDITIONAL INFORMATION

◊

单击下面可查看定价，库存，交付和生命周期等信息

>>ON Semiconductor(安森美)